

DESCRIPTION

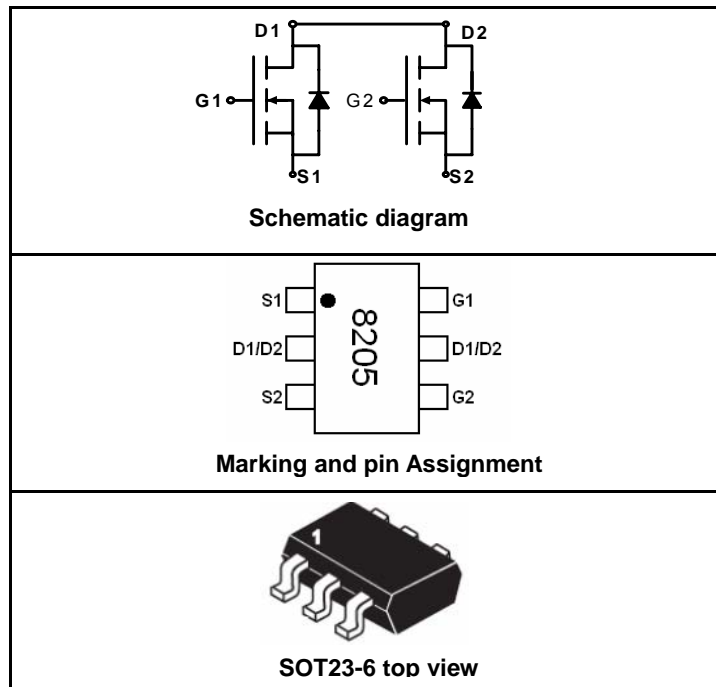
The SSF8205 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

GENERAL FEATURES

- $V_{DS} = 20V, I_D = 4A$
 $R_{DS(ON)} < 45m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 30m\Omega @ V_{GS}=4V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery protection
- Load switch
- Power management



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8205	SSF8205	SOT23-6	Ø180mm	8mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±10	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	4	A
	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	µA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			±100	nA

ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.8	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4V, I_D=4A$		27	30	m Ω
		$V_{GS}=2.5V, I_D=3A$		35	45	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=4A$		10		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$		800		PF
Output Capacitance	C_{oss}			155		PF
Reverse Transfer Capacitance	C_{rss}			125		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4V, R_{GEN}=10\Omega$		18.3		nS
Turn-on Rise Time	t_r			4.8		nS
Turn-Off Delay Time	$t_{d(off)}$			43.5		nS
Turn-Off Fall Time	t_f			20		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=4A,$ $V_{GS}=4V$		11		nC
Gate-Source Charge	Q_{gs}			2.2		nC
Gate-Drain Charge	Q_{gd}			2.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=2A$		0.8	1.2	V
Diode Forward Current (Note 2)	I_S				2	A

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

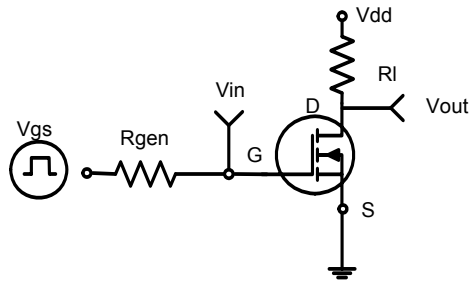


Figure 1: Switching Test Circuit

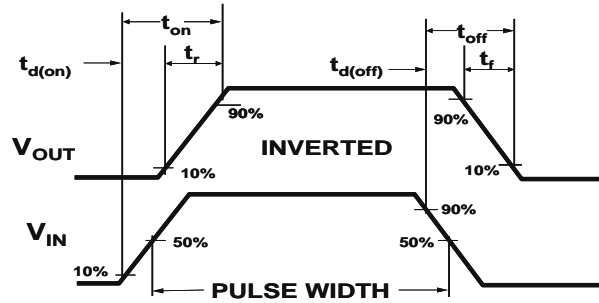


Figure 2: Switching Waveforms

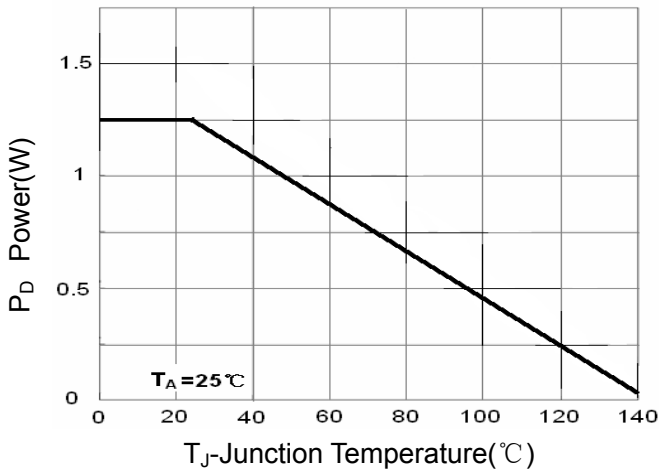


Figure 3 Power Dissipation

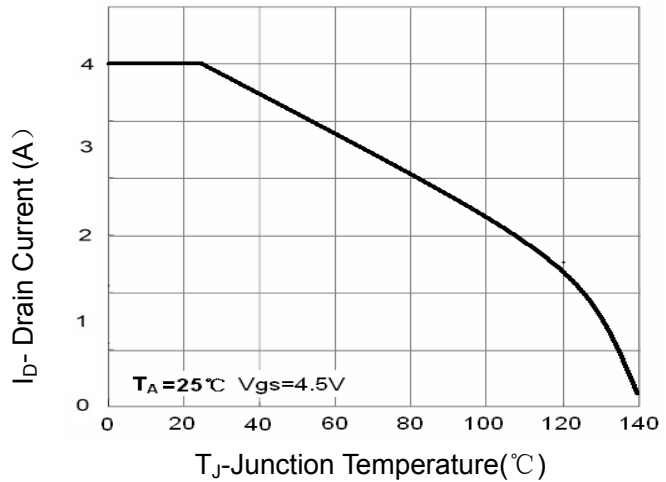


Figure 4 Drain Current

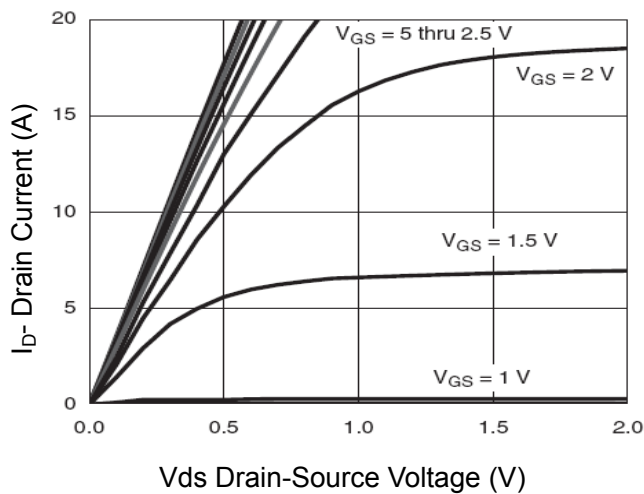


Figure 5 Output CHARACTERISTICS

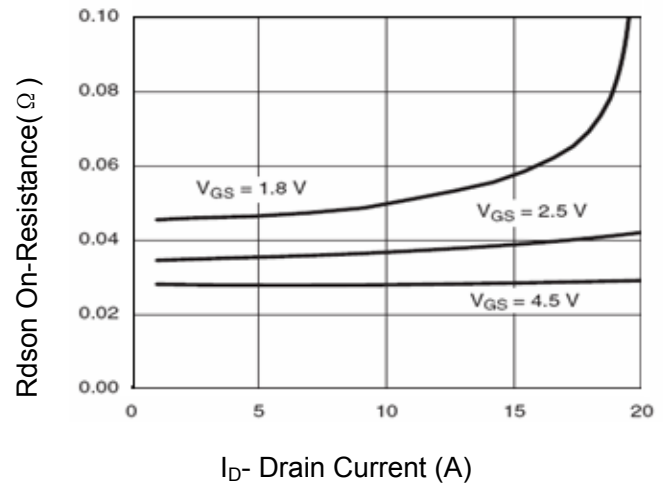


Figure 6 Drain-Source On-Resistance

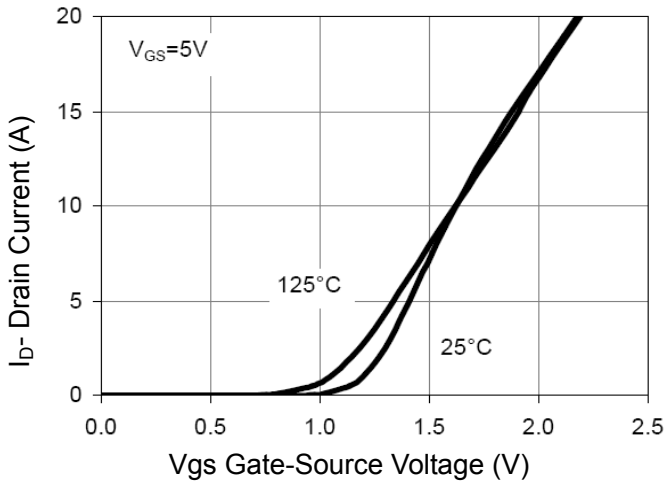


Figure 7 Transfer Characteristics

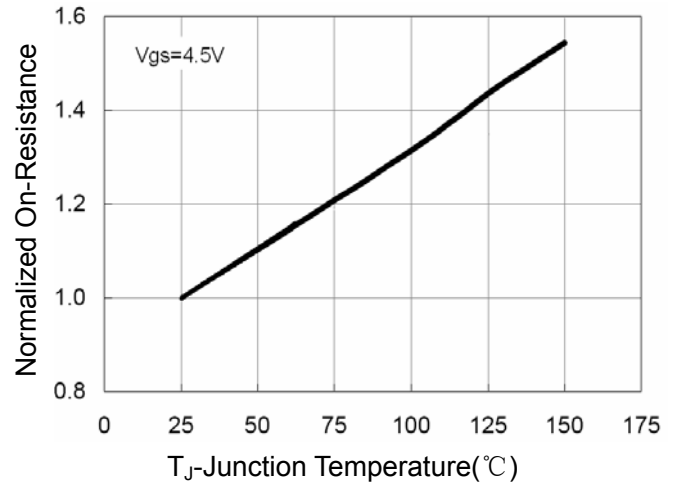


Figure 8 Drain-Source On-Resistance

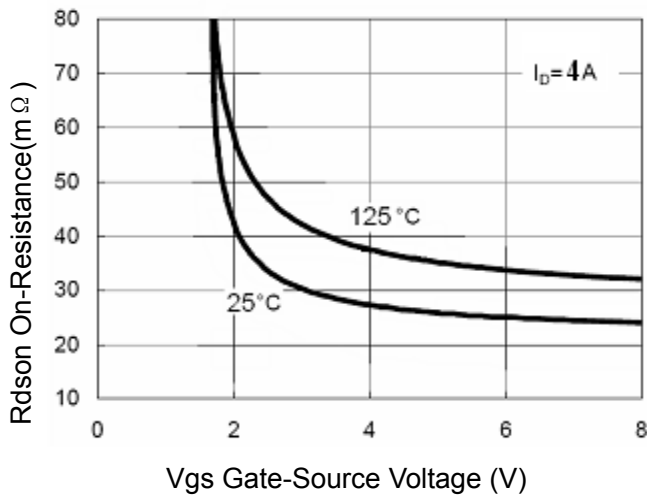


Figure 9 Rdson vs Vgs

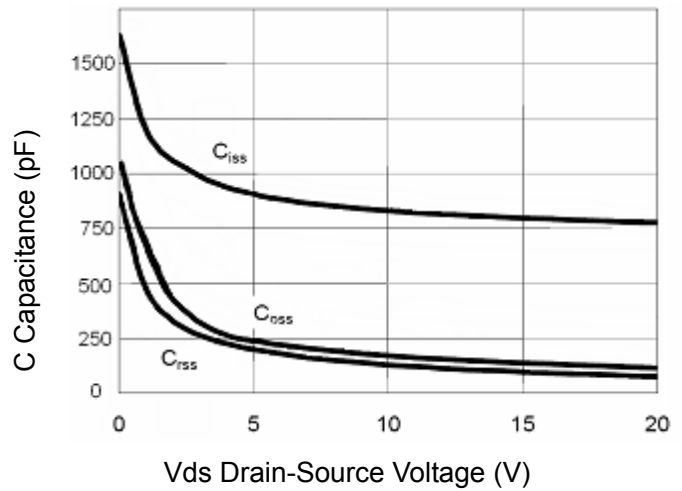


Figure 10 Capacitance vs Vds

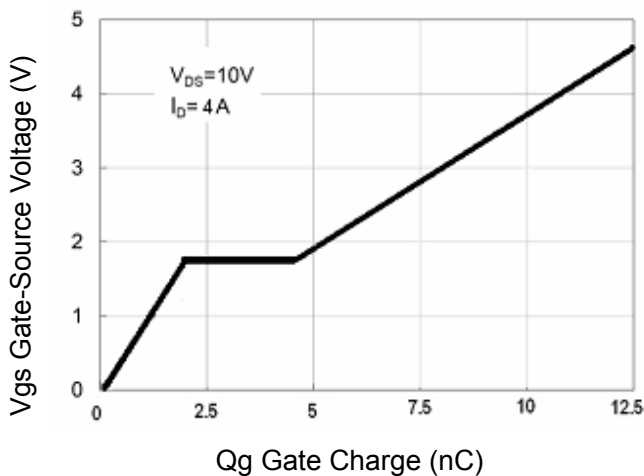


Figure 11 Gate Charge

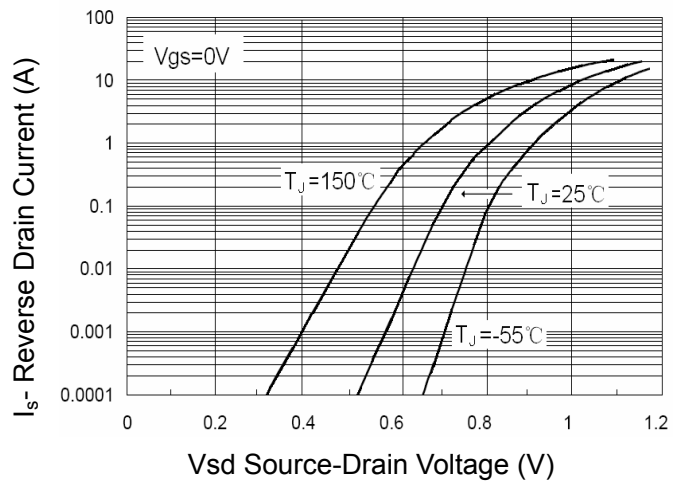


Figure 12 Source- Drain Diode Forward

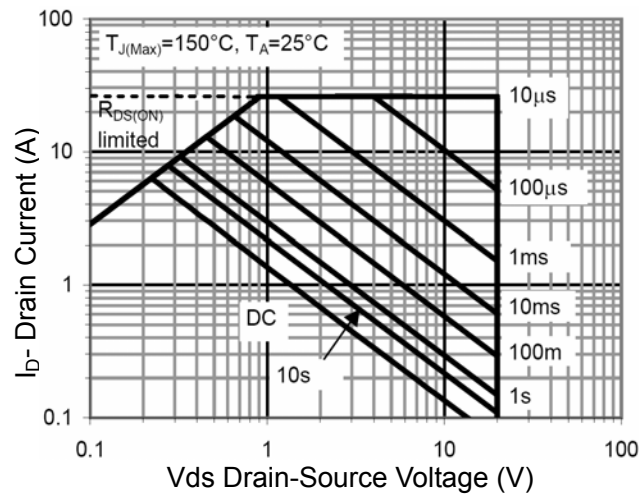


Figure 13 Safe Operation Area

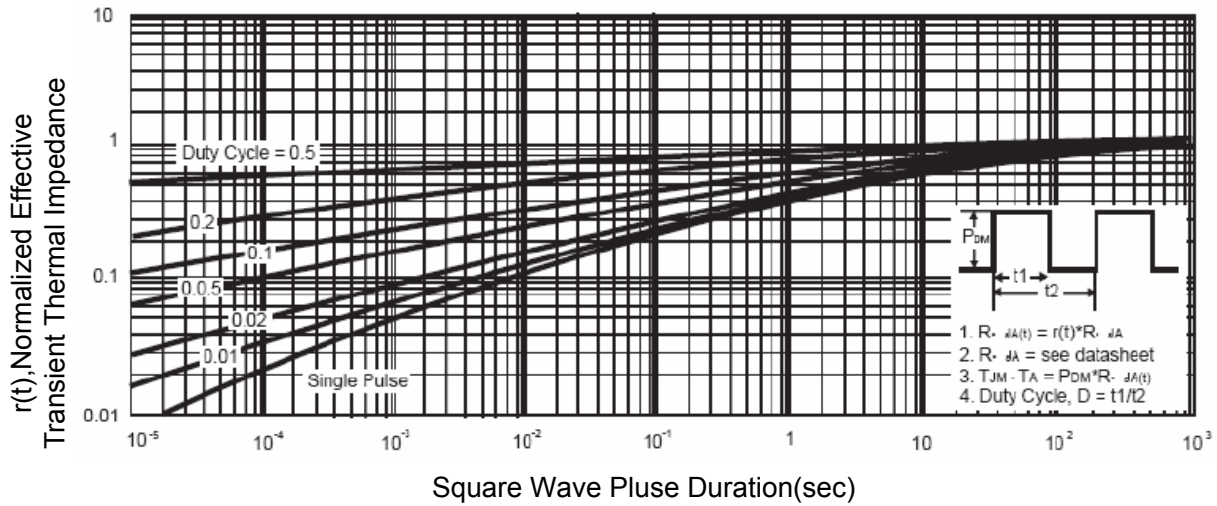
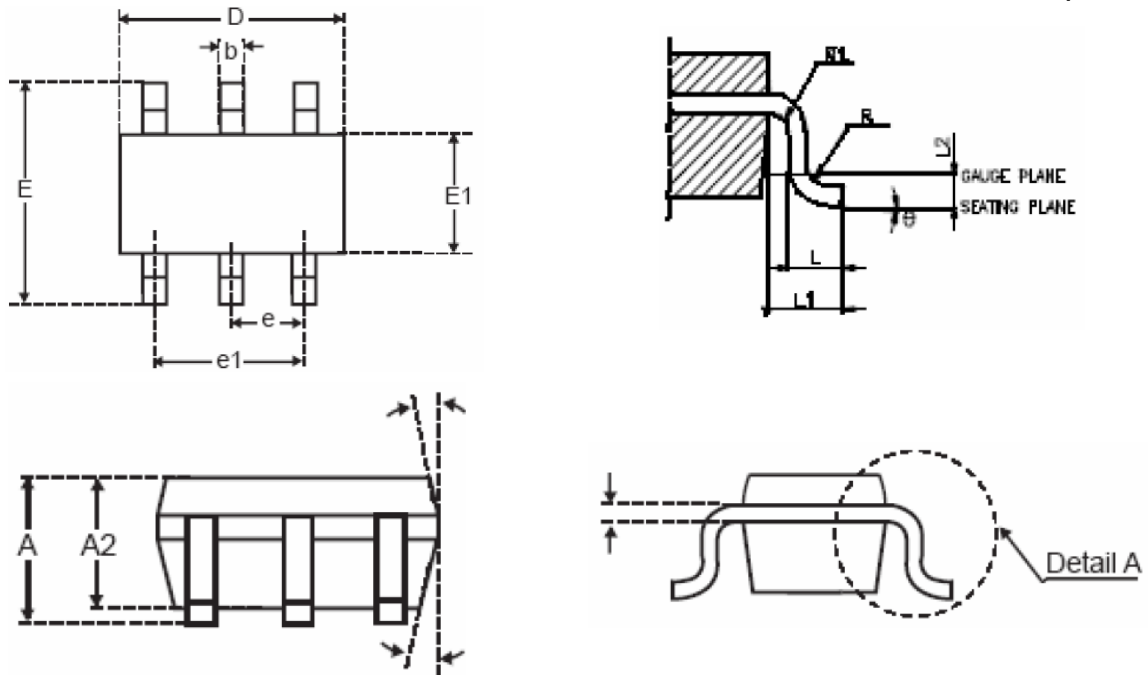


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT23-6 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A			1.45
A1			0.15
A2	0.90	1.15	1.30
b	0.30		0.50
c	0.08		0.22
D	2.90 BSC.		
E	2.80 BSC.		
E1	1.60 BSC.		
e	0.95 BSC.		
e1	1.90 BSC.		
L	0.30	0.45	0.60
L1	0.60 REF		
L2	0.25 BSC.		
R	0.10		
R1	0.10		0.25
θ	0°	4°	8°
θ_1	5°	10°	15°

NOTES:

1. All dimensions are in millimeters.
2. Dimensions are inclusive of plating
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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